Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	7	(organic same (switch$3 adj2 memory)) same (first adj3 electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/10 09:59
L2	24	(organic same (switch$3 adj2 memory)) and ((first adj3 electrod$2) same (organic adj3 memory))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/10 10:00
L3	89	(first adj2 electrod$2) and (organic adj4 memory) and (second electrod$2)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/10 10:00
L4	20	(((first adj2 electrod$2) and (organic adj3 memory) and (second electrod$2)) and diode) and (organic same (switch$4 adj2 memory))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/10 10:00
L5	8	(((((diode adj2 layer) near5 (second adj3 electrode)) near5 (first adj2 electrode)) near10 organic) and (memory or semiconductor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/10 10:00
L6	189	(((low or lower or first) adj3 electrode) same ((up or upper or high or second) adj2 electrode) same diode) same memory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/10 10:01
L7	6	((((low or lower or first) adj2 electrode) same ((up or upper or high or second) adj2 electrode) same diode) same memory) same (organic adj3 memory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/10 10:01
L8	16	((first adj3 electrode) same organic same diod$3) same (second adj3 electrode) same memory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/10 10:02
L9	3	morgan adj5 lewis adj6 bockius. as.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/10 10:10

L11	18	organic adj6 thin adj6 film adj10 switch$3.ti.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/10 10:16
L12	11	6 and 365/174,175.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/10 10:19
S1	10	organic adj3 switch$3 adj3 memory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/15 11:56
S2	115	organic same (switch$3 adj2 memory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/15 11:56
S3	5	(organic same (switch$3 adj2 memory)) same (first adj2 electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/10 09:59
S4	16	(first adj2 electrod$2) same (organic adj3 memory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/15 12:01
S5	11	(organic same (switch$3 adj2 memory)) and ((first adj2 electrod$2) same (organic adj3 memory))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/10 10:00
S6	39	(first adj2 electrod$2) and (organic adj3 memory) and (second electrod$2)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/10 10:00
S7	22	((first adj2 electrod$2) and (organic adj3 memory) and (second electrod$2)) and diode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/15 12:02
S8	11	((((first adj2 electrod$2) and (organic adj3 memory) and (second electrod$2)) and diode) and (organic same (switch$3 adj2 memory))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/10 10:00

S9	19	(diode adj2 layer) near5 (second adj2 electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/15 12:07
S10	15	((diode adj2 layer) near5 (second adj2 electrode)) near5 (first adj2 electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/15 12:07
S11	7	(((((diode adj2 layer) near5 (second adj2 electrode)) near5 (first adj2 electrode)) near10 organic) and (memory or semiconductor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/10 10:00
S12	14	((((diode adj2 layer) near5 (second adj2 electrode)) near5 (first adj2 electrode)) near10 organic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/15 12:09
S15	3784	((low or lower or first) adj2 electrode) same ((up or upper or high or second) adj2 electrode) same diode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/15 12:13
S16	141	(((low or lower or first) adj2 electrode) same ((up or upper or high or second) adj2 electrode) same diode) same memory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/10 10:01
S17	5	((((low or lower or first) adj2 electrode) same ((up or upper or high or second) adj2 electrode) same diode) same memory) same (organic adj2 memory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/10 10:01
S18	4	((((low or lower or first) adj2 electrode) same ((up or upper or high or second) adj2 electrode) same diode) same memory) same (organic adj2 layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/15 12:17
S19	36	((((low or lower or first) adj2 electrode) same ((up or upper or high or second) adj2 electrode) same diode) same memory) and "365"/$7.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/15 13:53
S20	104	organic adj2 switch$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/15 13:55

S21	17	(organic adj2 switch$3) and (first adj3 electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/15 13:56
S22	15	((organic adj2 switch$3) and (first adj3 electrode)) and (second adj3 electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/15 14:14
S23	219	(first adj3 electrode) same organic same diod$2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/15 13:59
S24	10	((first adj3 electrode) same organic same diod$2) same (second adj3 electrode) same memory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/10 10:02
S25	7	(organic adj2 switch$3) same (first adj3 electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/15 14:17
S26	2	("6055180").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/15 14:17
S27	73	"6055180"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/15 14:22
S28	23	tanabe-takahisa.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/15 14:23
S29	0	tanabe-takahisa-$.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/15 14:23